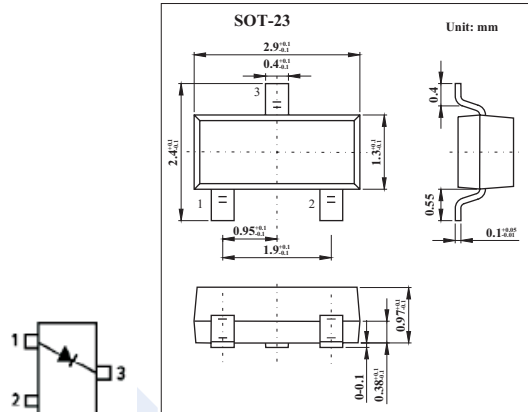


Silicon Epitaxial Planar Type

1SS370

■ Features

- Low forward voltage : $V_{F(3)} = 0.9 \text{ V(Typ)}$
- Fast reverse recovery time : $t_{rr} = 60\text{ns (MAX.)}$
- Small total capacitance : $C_T = 1.5 \text{ pF(Typ)}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	250	V
Reverse voltage	V_R	200	V
Average forward current	I_o	100	mA
Maximum (peak) forward current	I_{FM}	300	mA
Surge current (10 ms)	I_{FSM}	2	A
Power dissipation	P	100	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 + 125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	$V_{F(1)}$	$I_F = 10 \text{ mA}$		0.72	1.0	V
	$V_{F(2)}$	$I_F = 100 \text{ mA}$		0.90	1.2	
Reverse current	$I_{R(1)}$	$V_R = 50 \text{ V}$			0.1	μA
	$I_{R(2)}$	$V_R = 200 \text{ V}$			1.0	
Total capacitance	C_T	$V_R = 0, f = 1.0 \text{ MHz}$		1.5	3.0	pF
Reverse recovery time	t_{rr}	$I_F = 10 \text{ mA}$		10	60	ns

■ Marking

Marking	F5
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